

# Exam Summer Semester 2022

## Student Group

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# Exam Summer Semester 2022

## Additional permitted Aids

- non-programmable calculator,
- formulary (4 one-sided DIN A4 pages)

## Hits

- The duration of the exam is 120 min.
- Attempts to cheat will lead to exclusion and failure of the exam.
- Withdrawal is no longer possible after these exam has been handed out.
- Please write down intermediate calculations and results on the assignment sheet. (when more space is needed also on the reverse side. In this case: Mark it clearly).
- Always use units in the calculation.
- Use a document-proof, non-red pen.

## Only EEE1-relevant Part

This part is only for about 40 minutes !

### Exercise E2 Electrostatics I

(written test, approx. 10 % of a 120-minute written test, SS2022)

Given is the arrangement of three charges on the x-axis as shown in the picture below. The charges of the previous exercise are  $q_1 = 1.97 \cdot 10^{-9} \text{ As/m}$ . Which value needs  $E_4$  to have to get a resulting force of  $0 \text{ N}$  on  $q_0$ ?

Path:  $q_0 = -1 \text{ nC}$

- $q_1 = -2 \text{ nC}$

Path:  $E_4 = 230.97 \text{ V/m}$

$$\vec{F}_{01} = \left( \begin{array}{c} 19.97 \cdot 10^{-6} \text{ N} \\ 0 \\ 0 \end{array} \right)$$

In the beginning we are by components, we cannot calculate the resulting magnitude of the force.

$$|\vec{F}_{01}| = \sqrt{F_{01,x}^2 + F_{01,y}^2 + F_{01,z}^2} = \sqrt{(19.97 \cdot 10^{-6})^2 + 0 + 0} = 19.97 \cdot 10^{-6} \text{ N}$$

$$|\vec{F}_{01}| = |q_0| \cdot |E_4| \Rightarrow |E_4| = \frac{|\vec{F}_{01}|}{|q_0|} = \frac{19.97 \cdot 10^{-6} \text{ N}}{1 \cdot 10^{-9} \text{ C}} = 19.97 \cdot 10^3 \text{ V/m}$$

$$E_4 = 19.97 \cdot 10^3 \text{ V/m} = 19.97 \text{ kV/m}$$

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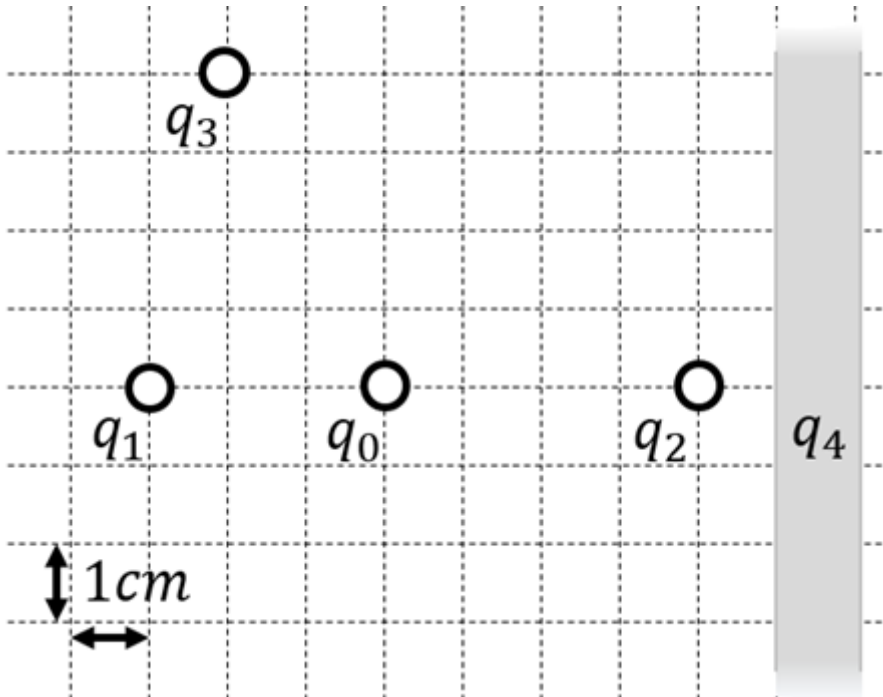
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1. Calculate the single forces  $\vec{F}_{01}$ ,  $\vec{F}_{02}$ ,  $\vec{F}_{03}$ , on the charge  $q_0$ !

Path

First, calculate the magnitude of the forces, like  $\vec{F}_{01}$ .

The force  $\vec{F}_{01}$  is purely on the  $x$ -axis and therefore equal to

$$\begin{aligned} F_{01,x} &= \frac{1}{4\pi\epsilon_0} \cdot \frac{q_1 \cdot q_0}{r_{01}^2} = \\ &= \frac{1}{4\pi \cdot 8.854 \cdot 10^{-12} \text{ As/Vm}} \cdot \frac{1 \cdot 10^{-9} \text{ C} \cdot 2 \cdot 10^{-9} \text{ C}}{(3 \cdot 10^{-2} \text{ m})^2} = \\ &= 19.97... \cdot 10^{-6} \frac{\text{As}^2 \cdot \text{Vm}}{\text{As} \cdot \text{m}^2} = 19.97... \cdot 10^{-6} \frac{\text{VA}}{\text{m}} \\ &= 19.97... \mu\text{N} \quad \text{(to the right)} \end{aligned}$$

Similarly, we get for  $\vec{F}_{02}$  and  $\vec{F}_{03}$

$$\begin{aligned} \vec{F}_{02} &= F_{02,x} = -28.09... \mu\text{N} \quad \text{(to the right)} \\ \vec{F}_{03} &= -22.47... \mu\text{N} \quad \text{(to the top left)} \end{aligned}$$

For  $\vec{F}_{03}$ , we have to calculate the  $x$ - and  $y$ -component.

This is possible, by using the angle  $\alpha$  between the line through  $q_0$  and  $q_3$  and the positive  $x$ -axis (pointing to the right).

So,  $\alpha$  has to be between  $90^\circ$  and  $180^\circ$ . It can be calculated by:

$$\begin{aligned} \alpha &= \arctan\left(\frac{-4 \text{ cm}}{+2 \text{ cm}}\right) = \pi - 1.1071... \\ &= 180^\circ - 63.4...^\circ = 116.6...^\circ \end{aligned}$$

Based on this, the  $x$ - and  $y$ -component is:

$$\begin{aligned} F_{03,x} &= |\vec{F}_{03}| \cdot \cos \alpha = 10.05... \mu\text{N} \quad \text{(to the left)} \\ F_{03,y} &= |\vec{F}_{03}| \cdot \sin \alpha = 20.10... \mu\text{N} \quad \text{(to the} \end{aligned}$$

top)} \\ \end{align\*}

**Exercise E4 Electrostatics II**  
**(written test, approx. 10 % of a 120-minute written test, SS2022)**

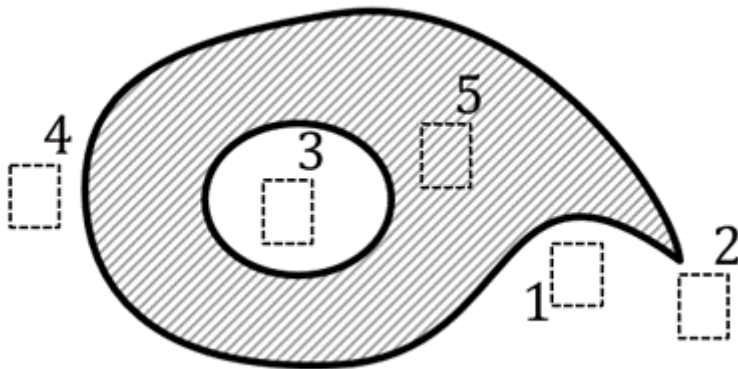
The figure below shows an arrangement of ideal metallic conductors (gray hatched) charged up to  $q = +1 \text{ nC}$ .

In white a dielectric (e.g. vacuum) is shown.

Several designated areas are shown by dashed frames and numbers  $x$ , which are partly inside the object.

Arrange the designated areas clearly according to ascending field strengths  $|\vec{E}_x|$  (absolute magnitude)!

Indicate also, if designated areas have quantitatively the same field strength.



Result

$$|E_3| = |E_5| = 0 < |E_1| < |E_4| < |E_2|$$

**Exercise E8 Capacitor**  
**(written test, approx. 7 % of a 120-minute written test, SS2022)**

Given the parallel plate capacitor shown in the left side of the figure with the following dimensions:  $d = 0.1 \text{ mm}$  of air ( $\epsilon_r = 1$ ), while the thickness of the dielectric material remains the same.  
 Length of layer overlap:  $l = 1.5 \text{ mm}$   
 Path

What is the new capacitance of the capacitor?  $d=1.0 \text{ ~}\mu\text{ m}$

Distance between plates  $d=1.0 \text{ ~}\mu\text{ m}$

Dielectric constant  $\epsilon_r=3$

The capacity can be derived from the geometry by using a parallel plate capacitor

$$C = \epsilon_r \epsilon_0 \frac{A}{d}$$

For the area  $A$  we have multiple plates with the area  $A_0 = l \cdot w$  facing each other.

The air adds another capacitor in series to the dielectric material. Therefore, the capacity can be calculated as 
$$C_{\text{Air}} = \frac{C \cdot C_{\text{Air}}}{C + C_{\text{Air}}}$$

The capacity of air is 
$$C_{\text{Air}} = \epsilon_0 \frac{N \cdot l \cdot w}{d_{\text{Air}}} = 8.854 \cdot 10^{-12} \text{ ~}\frac{\text{As}}{\text{Vm}} \cdot 1 \cdot \{5 \cdot 1.5 \cdot 10^{-3} \text{ ~}\text{m}\} \cdot \{0.7 \cdot 10^{-3} \text{ ~}\text{m}\} \cdot \{0.1 \cdot 10^{-6} \text{ ~}\text{m}\} = 0.465 \dots \text{ ~}\text{nF}$$

The material shall have a dielectric permittivity of  $\epsilon_r=3$ .

How many multiple plates  $N$  do we have to consider? For this, we have to count facing areas  $A_0$ . There are  $N=5$ .

$$\epsilon_r = 3$$

.. What is the field strength in the dielectric material between the layer, when a voltage of  $U=6.3 \text{ ~}\text{V}$  is applied?

Path

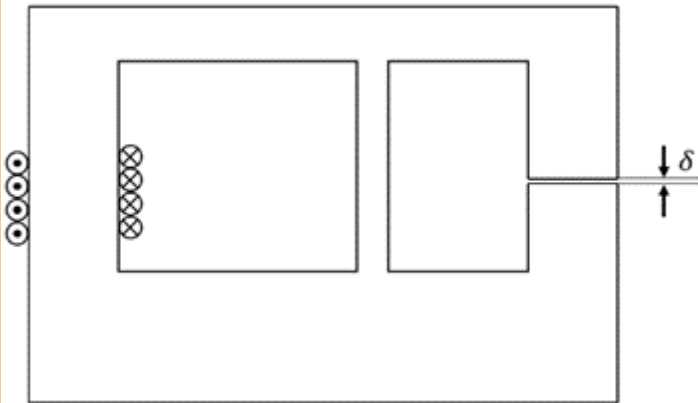
$$E = \frac{U}{d} = \frac{6.3 \text{ ~}\text{V}}{1 \cdot 10^{-6} \text{ ~}\text{m}}$$

$$C = \epsilon_r \epsilon_0 \frac{N \cdot l \cdot w}{d} = 8.854 \cdot 10^{-12} \text{ ~}\frac{\text{As}}{\text{Vm}} \cdot 3 \cdot \{5 \cdot 1.5 \cdot 10^{-3} \text{ ~}\text{m}\} \cdot \{0.7 \cdot 10^{-3} \text{ ~}\text{m}\} \cdot \{0.1 \cdot 10^{-6} \text{ ~}\text{m}\} = 0.465 \dots \text{ ~}\text{nF}$$

**Exercise E10 Magnetic Circuit**  
**(written test, approx. 7 % of a 120-minute written test, SS2022)**

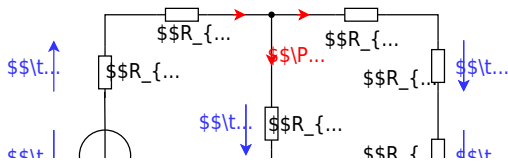
The magnetic setup below shall be given. Draw the equivalent magnetic circuit to represent the setup fully. Name all the necessary magnetic resistances, fluxes, and voltages. The components shall be designed in such a way, that the magnetic resistance is constant in it.

Formulas are not necessary.

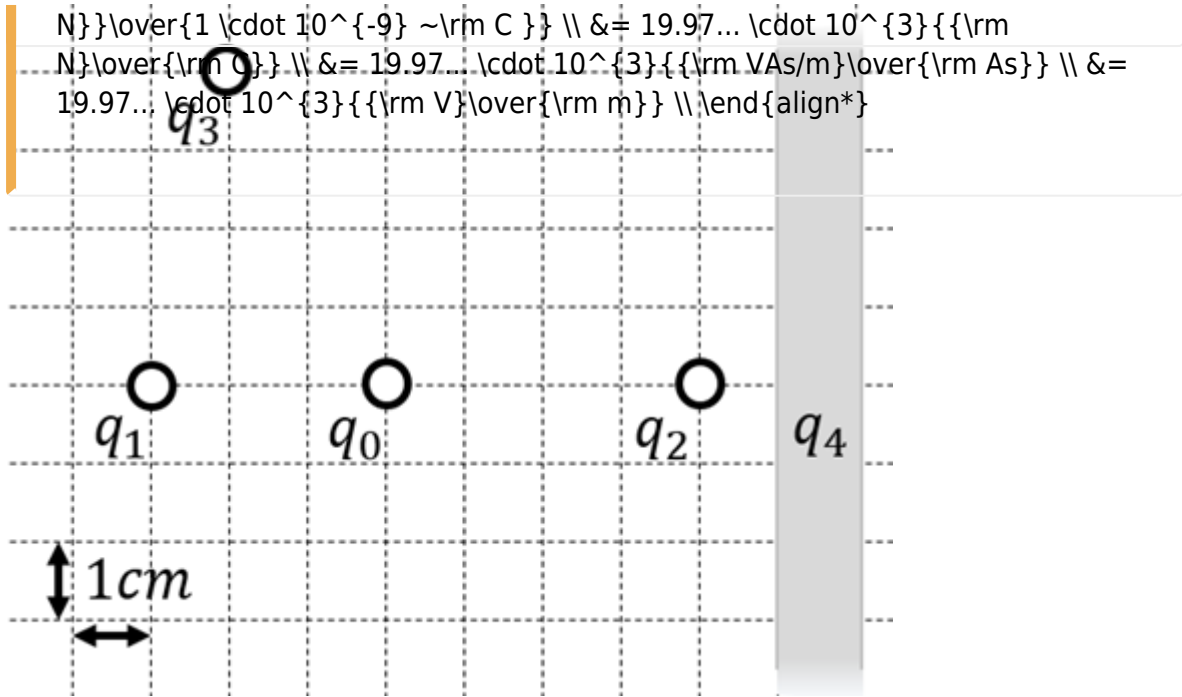


Path

Watch for parts of the magnetic circuit, where the width and material are constant. These parts represent the magnetic resistors which have to be calculated individually. Be aware, that every junction creates a branch with a new resistor, like for an electrical circuit - there must be a node on each "diversion".

$$R_{\text{m}} = \frac{1}{\mu_0 \mu_r} \frac{l}{w \cdot h}$$






1. Calculate the single forces  $\vec{F}_{01}$ ,  $\vec{F}_{02}$ ,  $\vec{F}_{03}$ , on the charge  $q_0$ !

Path

First, calculate the magnitude of the forces, like  $\vec{F}_{01}$ .  
 The force  $\vec{F}_{01}$  is purely on the  $x$ -axis and therefore equal to  $F_{01,x}$ . 
$$\vec{F}_{01} = F_{01,x} \hat{x} = \frac{1}{4\pi\epsilon_0} \cdot \frac{q_1 \cdot q_0}{r_{01}^2} \hat{x} = \frac{1}{4\pi \cdot 8.854 \cdot 10^{-12} \text{ As/Vm}} \cdot \frac{1 \cdot 1 \cdot 10^{-9} \text{ C} \cdot 2 \cdot 10^{-9} \text{ C}}{(3 \cdot 10^{-2} \text{ m})^2} = 19.97... \cdot 10^{-6} \frac{\text{As}^2 \cdot \text{Vm}}{\text{As} \cdot \text{cm}^2} = 19.97... \cdot 10^{-6} \frac{\text{VA}}{\text{m}} = 19.97... \cdot 10^{-6} \frac{\text{W}}{\text{m}} = 19.97... \mu\text{N} \quad \text{(to the right)}$$

Similarly, we get for  $\vec{F}_{02}$  and  $\vec{F}_{03}$  
$$\vec{F}_{02} = F_{02,x} \hat{x} = -28.09... \mu\text{N} \quad \text{(to the right)}$$
 
$$\vec{F}_{03} = -22.47... \mu\text{N} \quad \text{(to the top left)}$$

For  $\vec{F}_{03}$ , we have to calculate the  $x$ - and  $y$ -component. This is possible, by using the angle  $\alpha$  between the line through  $q_0$  and  $q_3$  and the positive  $x$ -axis (pointing to the right).

So,  $\alpha$  has to be between  $90^\circ$  and  $180^\circ$ . It can be calculated by: 
$$\alpha = \arctan\left(\frac{-4 \text{ cm}}{+2 \text{ cm}}\right) = \pi - 1.1071... = 180^\circ - 63.4...^\circ = 116.6...^\circ$$

Based on this, the  $x$ - and  $y$ -component is: 
$$F_{03,x} =$$

$$\begin{aligned} |\vec{F}_{03}| \cdot \cos \alpha &= 10.05 \dots \text{ (to the left)} \\ F_{03,y} &= |\vec{F}_{03}| \cdot \sin \alpha = 20.10 \dots \text{ (to the top)} \end{aligned}$$

[electrical\\_engineering\\_and\\_electronics:task\\_dtoqvpvrbdtdcozfk\\_with\\_calculation](#)  
[electrostatic](#), [field lines](#), [exam ee2 ss2022](#)

### Exercise E4 Electrostatics II

(written test, approx. 10 % of a 120-minute written test, SS2022)

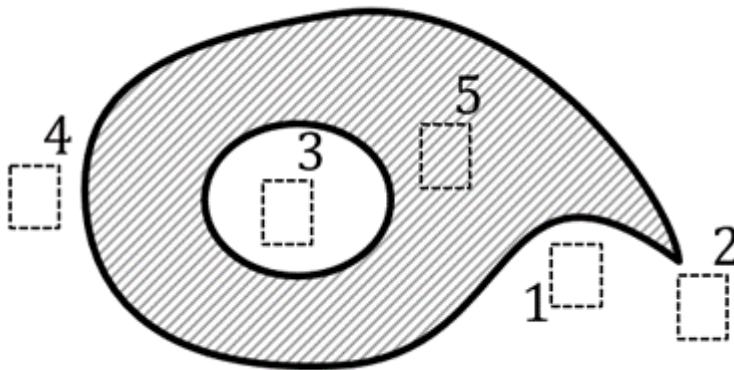
The figure below shows an arrangement of ideal metallic conductors (gray hatched) charged up to  $q = +1 \text{ nC}$ .

In white a dielectric (e.g. vacuum) is shown.

Several designated areas are shown by dashed frames and numbers  $x$ , which are partly inside the object.

Arrange the designated areas clearly according to ascending field strengths  $|\vec{E}_x|$  (absolute magnitude)!

Indicate also, if designated areas have quantitatively the same field strength.



Result

$$|E_3| = |E_5| = 0 < |E_1| < |E_4| < |E_2|$$

[electrical\\_engineering\\_and\\_electronics:task\\_ic9pioiu0notvwfp\\_with\\_calculation](#)  
[electrostatic](#), [electric field strength](#), [exam ee2 ss2022](#)

**Exercise E6 Electron Velocity in Semiconductors**  
**(written test, approx. 6 % of a 120-minute written test, SS2022)**

A current of  $I=1\text{ mA}$  flows through a cross-sectional area  $A=10\text{ }\mu\text{ m}^2$  in a semiconductor.

The electron density in the semiconductor is given by the number of dopant atoms per volume.

The doping shall provide 1 donor atom (= one electron) per  $10^{10}$  silicon atoms. The elementary charge is  $e = 1.602 \cdot 10^{-19}\text{ C}$  (about  $41\text{ }\mu\text{ s}$  of the speed of light). The molar volume of silicon is  $V_{\text{mol,Si}} = 12 \cdot 10^{-6}\text{ m}^3/\text{mol}$ , with  $N_{\text{A}} = 6.022 \cdot 10^{23}$  silicon atoms per  $1\text{ mol}$ .

The elementary charge is given as:  $e_0 = 1.602 \cdot 10^{-19}\text{ As}$

What is the average electron velocity  $v_e$  in this semiconductor?

Path

The following formula gives the speed, where  $n_e$  is the number of electrons per volume. 
$$v_e = \frac{I}{n_e \cdot e_0 \cdot A}$$

$n_e$  can be derived from the overall number of Si-atoms per volume ( $\frac{N_{\text{A}}}{V_{\text{mol,Si}}}$ ) and the fraction  $k_{\text{Donators}}$  of these atoms, which got substituted by donators. 
$$n_e = \frac{N_{\text{A}}}{V_{\text{mol,Si}}} \cdot k_{\text{Donators}} \cdot e_0 \cdot A$$

Putting in the numbers: 
$$v_e = \frac{1 \cdot 10^{-3}\text{ A}}{\frac{6.022 \cdot 10^{23}}{12 \cdot 10^{-6}\text{ m}^3/\text{mol}} \cdot 10^{-10} \cdot 1.602 \cdot 10^{-19}\text{ As} \cdot 10 \cdot 10^{-6}\text{ m}^2}$$

[electrical\\_engineering\\_and\\_electronics:task\\_tx86fewvysrcy8fc\\_with\\_calculation](#)  
[electrostatic](#), [electric field strength](#), [exam ee2 ss2022](#)

**Exercise E8 Capacitor**  
**(written test, approx. 7 % of a 120-minute written test, SS2022)**

Divide the total capacitance  $C$  into the left-side layer with the following width  $s_{\text{left}} = 0.1\text{ mm}$

Result:  $\epsilon_r = 1$  (air), while the thickness of the dielectric material is the same. Length of layer overlap:  $l = 1.5\text{ mm}$

Path: Distance between single layers:  $d = 1.0\text{ }\mu\text{ m}$

• Depth of component:  $w = 0.7\text{ mm}$   
 • Number of layers (from the picture): 3 left-side and 3 right-side layers.

Path

The capacity can be derived from the geometry by: 
$$C = \epsilon_0 \epsilon_r \frac{A}{d}$$

The air binds another capacitor in series to the dielectric material. Therefore, the capacity can be calculated as 
$$\frac{1}{C_{\text{Air}}} = \frac{1}{C_{\text{dielectric}}} + \frac{1}{C_{\text{air}}}$$

The capacity of air is 
$$C_{\text{Air}} = \epsilon_0 \frac{N \cdot l \cdot w}{d_{\text{air}}}$$
  
The material shall have a dielectric permittivity of  $\epsilon_r = 3$   
The following calculations shall ignore boundary effects on the end of the layers.

By this the overall capacity 
$$C = \epsilon_0 \frac{N \cdot l \cdot w}{d} \cdot \left( \frac{1}{\epsilon_r} + \frac{1}{\epsilon_{\text{air}}} \right)$$
  
How many "multiple plates"  $N$  do we have to consider?  
.. What is the field strength in the dielectric material between the plates, when a voltage of  $U = 6.3 \text{ V}$  is applied?

Path

The electric field strength  $E$  is given by: 
$$E = \frac{U}{d} = \frac{6.3 \text{ V}}{1 \cdot 10^{-6} \text{ m}}$$

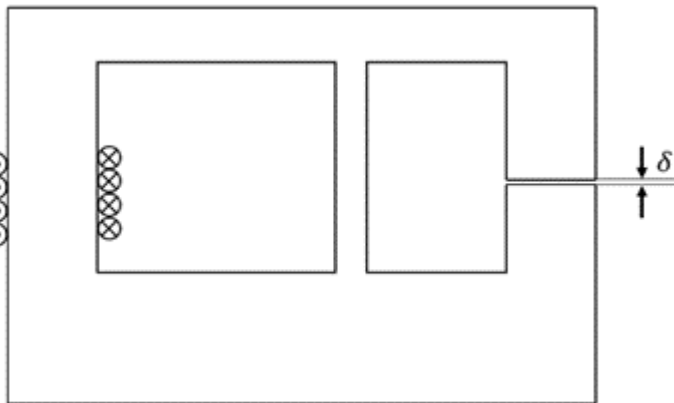
Therefore, the formula is 
$$C = \epsilon_0 \epsilon_r \frac{N \cdot l \cdot w}{d} = 8.854 \cdot 10^{-12} \text{ As/Vm} \cdot 3 \cdot \frac{5 \cdot 1.5 \cdot 10^{-3} \text{ m} \cdot 0.7 \cdot 10^{-3} \text{ m}}{1 \cdot 10^{-6} \text{ m}}$$

electrostatic, capacitor, plate capacitor, capacity, exam ee2 ss2022

**Exercise E10 Magnetic Circuit**  
**(written test, approx. 7 % of a 120-minute written test, SS2022)**

The magnetic setup below shall be given. Draw the equivalent magnetic circuit to represent the setup fully. Name all the necessary magnetic resistances, fluxes, and voltages.

The components shall be designed in such a way, that the magnetic resistance is constant in it.  
 Formulas are not necessary.



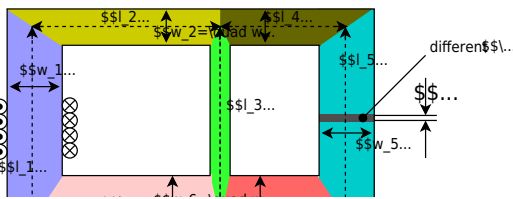
Path

Watch for parts of the magnetic circuit, where the width and material are constant.

These parts represent the magnetic resistors which have to be calculated individually.

Be aware, that every junction creates a branch with a new resistor, like for an electrical circuit - there must be a node on each "diversion".

$$R_{\text{m}} = \frac{l}{\mu_0 \mu_r w h}$$



electrical\_engineering\_and\_electronics:task\_yp4rbdlj8kktyrh\_p\_with\_calculation  
magnetic circuit, exam ee2 ss2022

**Exercise E12 Self Induction**  
**(written test, approx. 8 % of a 120-minute written test, SS2022)**

2. A voltage source with a maximum voltage of  $U = 50 \text{ V}$ , which the circuit breaker has a DC voltage source, which is fused with a circuit breaker.

Sketch the breaker part of the circuit ( $i(t=0) = 0 \text{ A}$ ) with a current of  $I = 0.3 \text{ A}$ . The inner resistance of the motor shall be neglected.)

The inner resistance of the motor shall be neglected.)

$$u_{\text{ind}}(t) = 3150 \text{ V}$$

Path

.. Draw the circuit (the circuit breaker can be drawn as a switch), with all voltage and current arrows.

For the maximum voltage on the circuit breaker one has to consider the following:

- external voltage of the voltage source  $U \text{ V}$
- voltage  $u_{\text{ind}}(t)$  induced by the change of the current

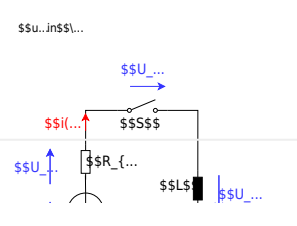
The first one is not given in the exercise, and therefore not considered here.

The induced voltage can be calculated by linearizing the following:

$$\begin{aligned} u_{\text{ind}}(t) &= -L \frac{di}{dt} \end{aligned}$$

$$\rightarrow u_{\text{ind}}(t) = -L \frac{\Delta i}{\Delta t}$$

$$\begin{aligned} u_{\text{ind}}(t) &= -L \frac{0 - I}{t_1 - t_0} \\ &= 50 \cdot 10^{-6} \cdot \frac{63 \text{ A}}{1 \cdot 10^{-6} \text{ s}} \\ &= 3150 \frac{\text{Vs}}{\text{A}} \cdot \frac{\text{A}}{\text{s}} \end{aligned}$$



electrical\_engineering\_and\_electronics:task\_unkkahm3u0v9azny\_with\_calculation self induction, induction, exam ee2 ss2022

**Exercise E14 Series Resonant Circuit (written test, approx. 10 % of a 120-minute written test, SS2022)**

2. What is the resonance frequency of the series RLC circuit with the parameters  $R = 10 \text{ } \Omega$ ,  $L = 100 \text{ } \mu\text{H}$ , and  $C = 100 \text{ nF}$ ? Result:  $f_r = 159.15 \text{ kHz}$

At resonance, the magnitude of the impedance  $Z_{\text{RLC}}$  would be  $X_{C0} = Z_{\text{RLC}}$ . Which value would  $C_0$  have for the given  $f_0$ ?

- Path:  $C = 10 \text{ nF}$
- Path:  $C = 100 \text{ nF}$
- Path:  $C = 10 \text{ } \mu\text{F}$
- Path:  $C = 100 \text{ } \mu\text{F}$

$$f_r = \frac{1}{2\pi\sqrt{LC}} \Rightarrow \frac{1}{2\pi\sqrt{60 \cdot 10^{-12} \cdot C}} = 159.15 \text{ kHz}$$

$$Z_{\text{RLC}} = X_{C0} \Rightarrow \frac{1}{2\pi f C} = R$$

$$C = \frac{1}{2\pi \cdot 100 \cdot 10^6 \cdot 10} = 10.6 \text{ nF}$$



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